

# FGW30N60VD

**Discrete IGBT** 

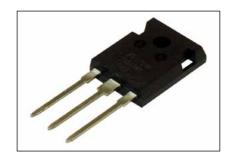
## **Discrete IGBT (High-Speed V series)** 600V / 30A

### ■ Features

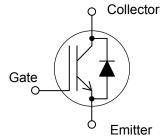
Low power loss Low switching surge and noise High reliability, high ruggedness (RBSOA, SCSOA etc.)

### Applications

Inverter for Motor drive AC and DC Servo drive amplifier Uninterruptible power supply



### Equivalent circuit



### ■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at T<sub>c</sub>=25°C unless otherwise specified)

| Items                                 | Symbols             | Characteristics | Units | Remarks                       |
|---------------------------------------|---------------------|-----------------|-------|-------------------------------|
| Collector-Emitter voltage             | Vces                | 600             | V     |                               |
| Gate-Emitter voltage                  | V <sub>GES</sub>    | ±20             | V     |                               |
| DC Collector Current                  | Ic@25               | 55              | Α     | Tc=25°C, Tj=150°C             |
|                                       | Ic@100              | 30              | Α     | Tc=100°C, Tj=150°C            |
| Pulsed Collector Current              | I <sub>CP</sub>     | 60              | Α     | Note *1                       |
| Turn-Off Safe Operating Area          | -                   | 60              | Α     | Vce≤600V, Tj≤175°C            |
| Diode Forward Current                 | F@25                | 48              | Α     |                               |
|                                       | IF@100              | 25              | Α     |                               |
| Diode Pulsed Current                  | I <sub>FP</sub>     | 60              | Α     | Note *1                       |
| Short Circuit Withstand Time          | tsc                 | 10              | μs    | Vcc≤320V, VgE=15V<br>Tj≤150°C |
| IGBT Max. Power Dissipation           | P <sub>D_IGBT</sub> | 230             | W     | Tc=25°C                       |
| FWD Max. Power Dissipation            | P <sub>D_FWD</sub>  | 125             | VV    | Tc=25°C                       |
| <b>Operating Junction Temperature</b> | T <sub>j</sub>      | -40~+175        | °C    |                               |
| Storage Temperature                   | T <sub>stg</sub>    | -55~+175        | °C    |                               |

Note \*1 : Pulse width limited by Tjmax.

● Electrical characteristics (at T<sub>j</sub>= 25°C unless otherwise specified)

| Items                                | Symbols               | Conditions                                    | Ch   | Characteristics |      |      |  |  |
|--------------------------------------|-----------------------|---|--|-----------------|------|------|--|--|
|                                      | ,                     |   | min.   | typ.            | max. | Unit |  |  |
| Collector-Emitter Breakdown Voltage  | V <sub>(BR)CES</sub>  | $I_{C} = 250 \mu A, V_{GE} = 0 V$             | 600  | -               | -    | V    |  |  |
| Zero Gate Voltage Collector Current  | Ices                  | V <sub>CE</sub> = 600V, V <sub>GE</sub> = 0V  | -  | -               | 250  | μA   |  |  |
|                                      |                       | I <sub>j</sub> =1/5°C                         | -  | -               | 10   | mA   |  |  |
| Gate-Emitter Leakage Current         | IGES                  | $V_{CE} = 0V, V_{GE} = \pm 20V$               | -  | -               | 200  | nA   |  |  |
| Gate-Emitter Threshold Voltage       | V <sub>GE (th)</sub>  | V <sub>CE</sub> = +20V, I <sub>C</sub> = 30mA | 6.2  | 6.7             | 7.2  | V    |  |  |
| Collector-Emitter Saturation Voltage | V <sub>CE (sat)</sub> | $V_{GE} = +15V$ , $I_{C} = 30A$               | -  | 1.60            | 2.05 | V    |  |  |
| Input Capacitance                    | Cies                  | V <sub>CF</sub> =25V   T <sub>J</sub> =175°C  | -  | 2.1<br>1910     | -    |      |  |  |
| Output Capacitance                   | Coes                  | V <sub>GE</sub> =0V                           | <del>-</del>                                     | 145             | _    | pF   |  |  |
| Reverse Transfer Capacitance         | Cres                  | f=1MHz  | _  | 105             | _    | Pi   |  |  |
| Neverse transfer Supacitance         | Oles                  | V <sub>cc</sub> = 400V                        |  | 100             |      |      |  |  |
| Gate Charge                          | Q <sub>G</sub>        | Ic = 30A                                      | _  | 225             | -    | nC   |  |  |
|                                      |                       | V <sub>GE</sub> = 15V                         |  |                 |      |      |  |  |
| Turn-On Delay Time                   | t <sub>d(on)</sub>    | T <sub>j</sub> = 25°C                         | -  | 35              | -    |      |  |  |
| Rise Time                            | t                     | Vcc = 400V                                    | -  | 60              | -    | ns   |  |  |
| Turn-Off Delay Time                  | t <sub>d(off)</sub>   | Ic = 30A                                      | -  |                 |      |      |  |  |
| Fall Time                            | tr                    | V <sub>GE</sub> = 15V                         | -  | 38              | -    | 1    |  |  |
| Turn-On Energy                       | Eon                   | $R_G = 10\Omega$                              | -  | 1.2             | -    | mJ   |  |  |
| Turn-Off Energy                      | Eoff                  | L = 500µH                                     |  | - 0.7           | -    |      |  |  |
|                                      |                       | Energy loss include "tail" and FWD reverse    | -  |                 |      |      |  |  |
|                                      |                       | recovery.                                     |  |                 |      |      |  |  |
| Turn-On Delay Time                   | t <sub>d(on)</sub>    | T <sub>j</sub> = 175°C                        | -  | 36              | -    |      |  |  |
| Rise Time                            | t                     | V <sub>cc</sub> = 400V                        | -  | 60              | -    | ns   |  |  |
| Turn-Off Delay Time                  | t <sub>d(off)</sub>   | $I_{C} = 30A$ $V_{GE} = 15V$                  | -  | 235             | -    |      |  |  |
| Fall Time                            | t <sub>r</sub>        | $V_{GE} = 15V$ $R_G = 10\Omega$               | -  | 50              | -    |      |  |  |
| Turn-On Energy                       | Eon                   | L = 500µH                                     | -  | 2.0             | -    |      |  |  |
| Turn-Off Energy                      | Eoff                  | Energy loss include "tail" and FWD reverse    | _  | 1.2             | -    | mJ   |  |  |
|                                      | Coff                  | recovery.                                     | -  |                 |      |      |  |  |
|                                      |                       | T-25°C  | <u> </u>   | 1.5             | 1.95 | V    |  |  |
| Forward Voltage Drop                 | VF                    | I⊧=25A T <sub>i</sub> =175°C                  | <del>                                     </del> | 1.3             | -    | V    |  |  |
|                                      |                       | V <sub>cc</sub> =30V                          |  | 1.0             |      | v    |  |  |
| Diode Reverse Recovery Time          | t <sub>rr1</sub>      | I <sub>F</sub> = 2.5A                         | _  | 40              | 52   | ns   |  |  |
|                                      |                       | -di/dt=200A/µs                                |  |                 |      |      |  |  |
|                                      |                       | V <sub>cc</sub> =400V                         |  | 0.00            |      |      |  |  |
| Diode Reverse Recovery Time          | t <sub>rr2</sub>      | I <sub>F</sub> =25A                           | -  | 0.30            | -    | μs   |  |  |
| Diada Bayaraa Baaayary Charga        |                       | -di⊧/dt=200A/µs                               |  | 0.70            |      | μC   |  |  |
| Diode Reverse Recovery Charge        | Qrr                   | T <sub>j</sub> =25°C                          | -  | 0.70            | -    | μΟ   |  |  |

FGW30N60VD

http://www.fujielectric.com/products/semiconductor/

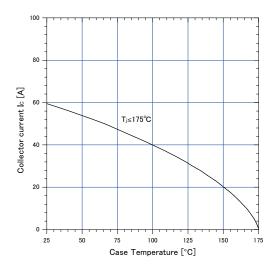
| Items                         | Symbols | Conditions                      | Characteristics |      |      | Unit |
|-------------------------------|---------|---------------------------------|-----------------|------|------|------|
|                               |         |                                 | min.            | typ. | max. | Unit |
| Diode Reverse Recovery Time   | trr2    | Vcc=400V<br>I <sub>F</sub> =25A | -               | 0.44 | -    | μs   |
| Diode Reverse Recovery Charge | Qrr     | -di⊧/dt=200A/μs<br>T:=175°C     | -               | 2.7  | -    | μC   |

### ● Thermal resistance

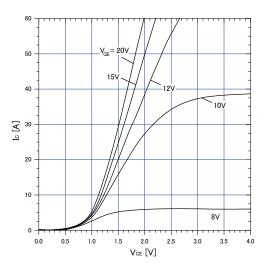
| Items                                     | Symbols                   |      | Unit |       |       |
|---|---------------------------|------|------|-------|-------|
| items                                     | Symbols                   | min. | typ. | max.  | Oilit |
| Thermal Resistance, Junction-Ambient      | R <sub>th(j-a)</sub>      | -    | -    | 50    |       |
| Thermal Resistance, IGBT Junction to Case | R <sub>th(j-c)_IGBT</sub> | -    | -    | 0.641 | °C/W  |
| Thermal Resistance, FWD Junction to Case  | R <sub>th(j-c)_FWD</sub>  | -    | -    | 1.191 |       |

### **■** Characteristics (Representative)

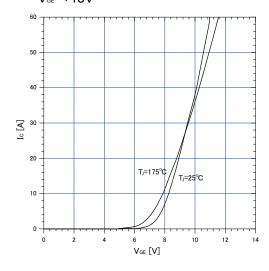
Graph.1 DC Collector Current vs  $T_c$   $V_{ce} \ge +15V$ ,  $T_i \le 175$ °C



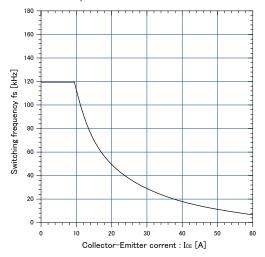
Graph.3 Typical Output Characteristics ( $V_{\text{CE}}$ - $I_{\text{C}}$ )  $T_{\text{J}}$ =25°C



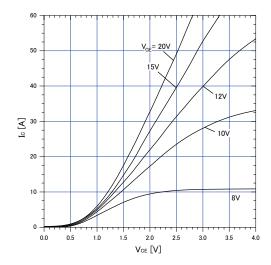
Graph.5 Typical Transfer Characteristics  $V_{\text{GE}}$ =+15V



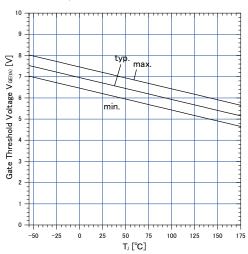
Graph.2 Collector Current vs. switching frequency  $V_{\text{og}}$ =+15V,  $T_{\text{o}}$ ≤175°C,  $V_{\text{co}}$ =400V, D=0.5,  $R_{\text{o}}$ =10 $\Omega$ ,  $T_{\text{o}}$ =100°C



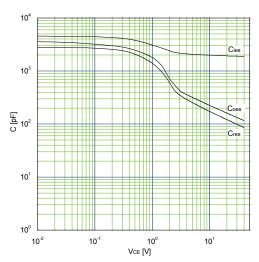
Graph.4 Typical Output Characteristics ( $V_{ce}$ - $I_c$ )  $T_j$ =175°C



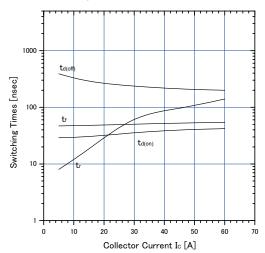
Graph.6
Gate Threshold Voltage vs. T<sub>i</sub>
I<sub>c</sub>=30mA, V<sub>cr</sub>=20V



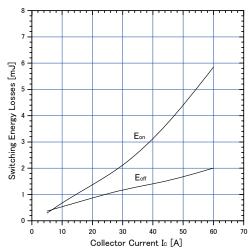
Graph.7 Typical Capacitance V<sub>c∈</sub>=0V, f=1MHz, T<sub>i</sub>=25°C



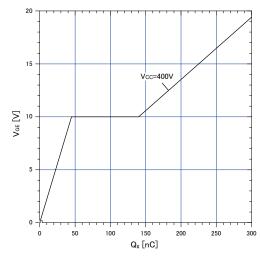
Graph.9
Typical switching time vs.  $I_c$   $T_i$ =175°C,  $V_{cc}$ =400V, L=500 $\mu$ H  $V_{ce}$ =15V, $R_c$ =10 $\Omega$ 



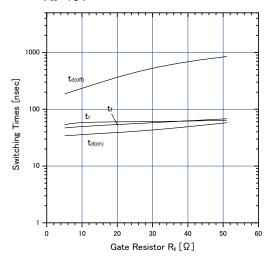
Graph.11 Typical switching losses vs.  $I_c$  T<sub>J</sub>=175°C,  $V_{cc}$ =400V, L=500 $\mu$ H  $V_{ce}$ =15V,  $R_c$ =10 $\Omega$ 



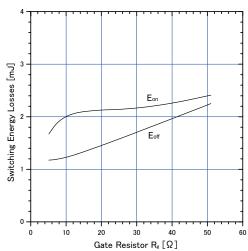
Graph.8 Typical Gate Charge Vcc=400V, Ic=30A, T,=25°C



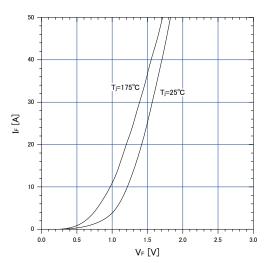
Graph.10 Typical switching time vs.  $R_{\rm s}$  T<sub>1</sub>=175°C,  $V_{\rm cc}$ =400V,  $I_{\rm c}$ =30A, L=500 $\mu$ H  $V_{\rm ce}$ =15V



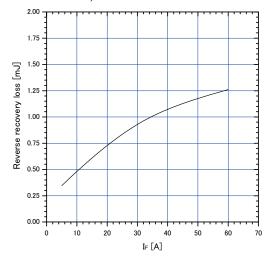
Graph.12 Typical switching losses vs.  $R_{\rm s}$  T<sub>i</sub>=175°C,  $V_{\rm cc}$ =400V,  $I_{\rm c}$ =30A, L=500 $\mu$ H  $V_{\rm ge}$ =15V



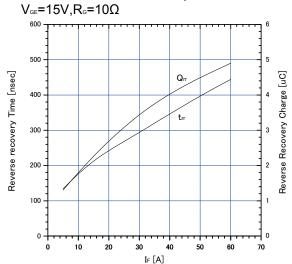
Graph.13 FWD Forward voltage drop (V<sub>F</sub>-I<sub>F</sub>)



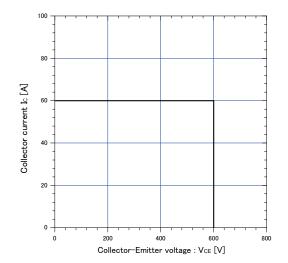
Graph.15 Typical reverse recovery loss vs. I<sub>F</sub> T<sub>i</sub>=175°C,V<sub>CC</sub>=400V,L=500 $\mu$ H V<sub>GE</sub>=15V,R<sub>G</sub>=10 $\Omega$ 



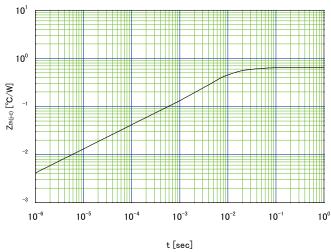
Graph.14
Typical reverse recovery characteristics vs. I<sub>F</sub>
T<sub>i</sub>=175°C, V<sub>∞</sub>=400V, L=500µH,



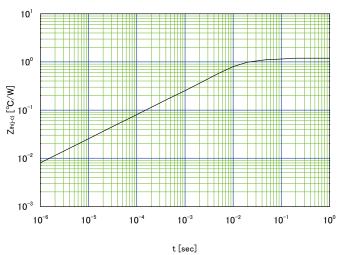
Graph.16 Reverse biased Safe Operating Area  $T_i \le 175^{\circ}C$ ,  $V_{oe} = +15V/0V$ ,  $R_o = 10\Omega$ 



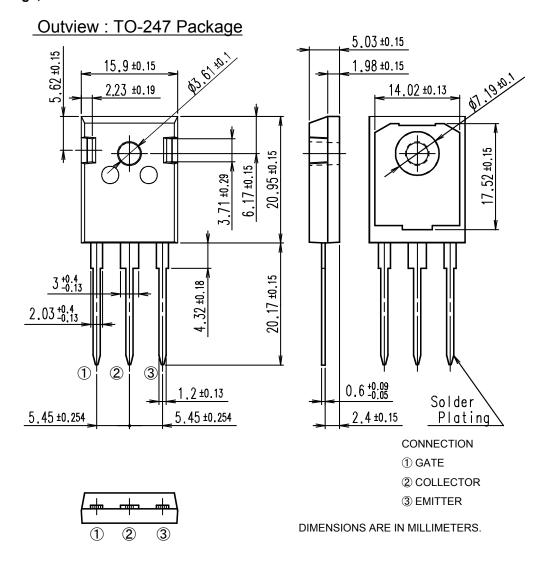
Graph.17
Transient thermal resistance of IGBT



Graph.18
Transient thermal resistance of FWD



### ■ Outline Drawings, mm



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